

Electronic Supplementary Information

Nanosheet thickness-modulated MoS₂ dielectric property evidenced by field-effect transistor performance

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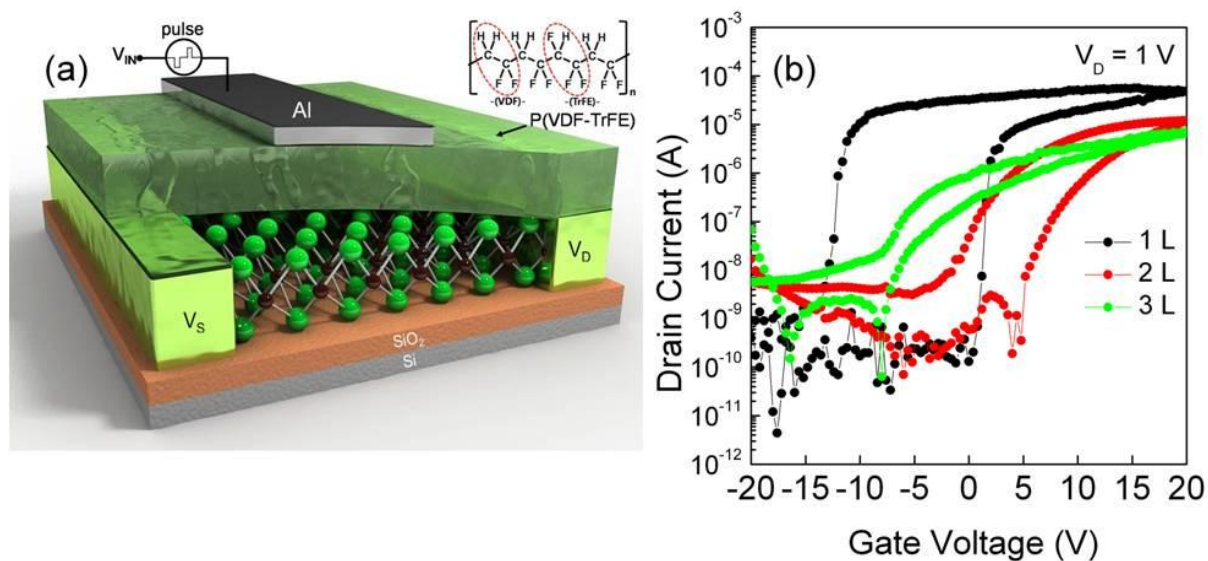


Fig. S1 (a) 3D schematic and transfer curves of MoS₂ memory FETs with P(VDF-TrFE) ferroelectric polymer. According to (b) the transfer curves of our memory FETs, the FET with single layer MoS₂ channel shows the most superior SS property while the SS properties degrade with the MoS₂ thickness as shown from double- and triple-layer devices, supporting our main results from top-gate MoS₂ FETs with Al₂O₃ dielectrics. (As another result following the SS degradation, we can see that the memory window gets reduced.)